Silicon NPN Power Transistors 2SD2331

DESCRIPTION

- With TO-3PFa package
- High voltage;high speed
- Built-in damper diode

APPLICATIONS

- For color TV horizontal output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

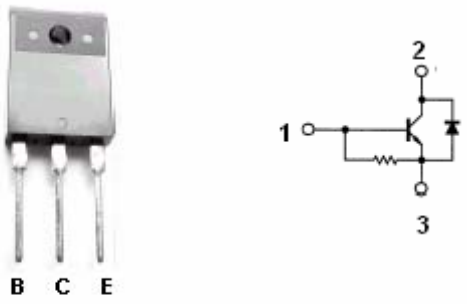


Fig.1 simplified outline (TO-3PFa) and symbol

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	600	V
V_{EBO}	Emitter-base voltage		5	V
I_C	Collector current		3.5	A
I_B	Base current		1	A
P_C	Collector power dissipation	T_C=25℃	40	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=200mA , I_C=0	5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=3A; I_B=0.8A		3.0	5.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=3A ;I_B=0.8A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=800V I_E=0			10	μA
h_{FE}	DC current gain	I_C=0.5A ; V_{CE}=5V	8			
f_T	Transition frequency	I_C=0.1A ; V_{CE}=10V		3		MHz
V_F	Diode forward voltage	I_F=3.5A			2.0	V

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PACKAGE OUTLINE

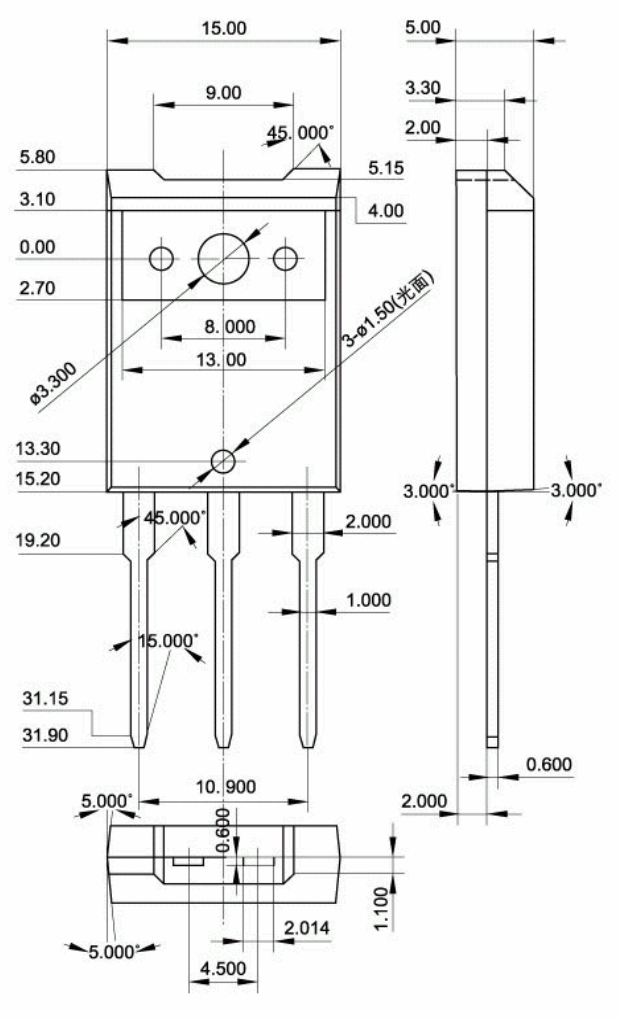


Fig.2 Outline dimensions (unindicated tolerance:±0.30mm)